

Dual N-Channel Power MOSFET

20V, 5.8A, 25mΩ

Features

- Halogen-Free according to IEC 61249-2-21
- Suited for 1.8V drive applications
- Low profile package
- RoHS Compliant

APPLICATION

- Battery Pack
- Load Switch

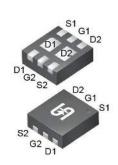
KEY PERFORMANCE PARAMETERS				
PARAME	TER	VALUE	UNIT	
V_{DS}		20	V	
	$V_{GS} = 4.5V$	25		
R _{DS(on)} (max)	$V_{GS} = 2.5V$	35	mΩ	
	$V_{GS} = 1.8V$	55		
Qg		7.7	nC	

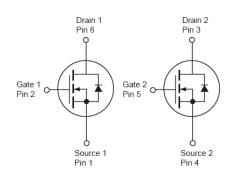












Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	±10	V
Continuous Drain Current (Note 1)	$T_{\rm C} = 25^{\circ}{\rm C}$	5.8	^	
Continuous Drain Current	$T_C = 100$ °C	I _D	3.48	Α
Pulsed Drain Current (Note 2)		I _{DM}	23.2	Α
Total Power Dissipation @ $T_C = 25^{\circ}C$		P _{DTOT}	0.62	W
Operating Junction and Storage Temperature Range		T_J, T_STG	- 55 to +150	°C

THERMAL PERFORMANCE			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Ambient Thermal Resistance	R _{OJA}	200	°C/W

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air.

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ELECTRICAL SPECIFICAT						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 3)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	$V_{GS(TH)}$	0.4	0.6	0.8	٧
Gate Body Leakage	$V_{GS} = \pm 10V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS}=16V, V_{GS}=0V$	I _{DSS}			1	μΑ
	$V_{GS} = 4.5V, I_D = 4A$			20	25	
Drain-Source On-State Resistance	$V_{GS} = 2.5V, I_D = 3A$	R _{DS(on)}		27	35	mΩ
	$V_{GS} = 1.8V, I_D = 2A$			39	55	
Forward Transconductance	$V_{DS}=10V$, $I_{D}=3A$	9 _{fs}		6.5		S
Dynamic (Note 4)		•				
Total Gate Charge		Q_g		7.7	11	
Gate-Source Charge	$V_{DS} = 10V, I_D = 4A,$	Q_{gs}		0.9	1	nC
Gate-Drain Charge	$V_{GS} = 4.5V$	Q_{gd}		2.4	5	
Input Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	C _{iss}		535	775	
Output Capacitance		C _{oss}		60	85	pF
Reverse Transfer Capacitance	7 T = 1.0IVIF12	C_{rss}		34	50	
Switching (Note 5)						
Turn-On Delay Time		t _{d(on)}		4.1	8	
Turn-On Rise Time	$V_{DD} = 10V, I_{D} = 1A,$	t _r		11.6	22	
Turn-Off Delay Time	$V_{GS} = 4.5V, R_G = 25\Omega$	t _{d(off)}		23.9	45	ns
Turn-Off Fall Time	1	t _f		7.6	14	
Source-Drain Diode (Note 3)		•		•	•	
Continuous Source Current		I _S			5.8	Α
ulsed Source Current		I _{SM}			23.2	Α
Forward On Voltage	$V_{GS} = 0V, I_{S} = 1A$	V _{SD}			1	V

Notes:

- 1. Current limited by package.
- 2. Pulse width limited by the maximum junction temperature.
- 3. Pulse test: PW \leq 300 μ s, duty cycle \leq 2%.
- 4. For DESIGN AID ONLY, not subject to production testing.
- 5. Switching time is essentially independent of operating temperature.

ORDERING INFORMATION

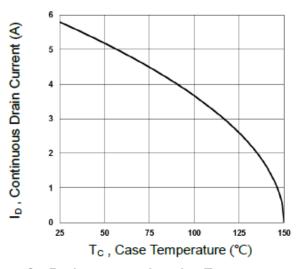
PART NO.		PACKAGE	PACKING		
	TSM250N02DCQ RFG	TDFN 2x2	3,000pcs / 7" Reel		



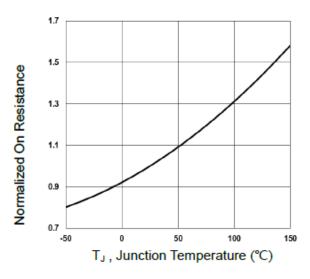
CHARACTERISTICS CURVES

(T_C = 25°C unless otherwise noted)

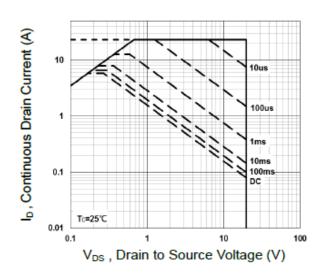
Continuous Drain Current vs. Tc



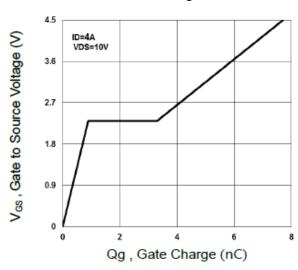
On-Resistance vs. Junction Temperature



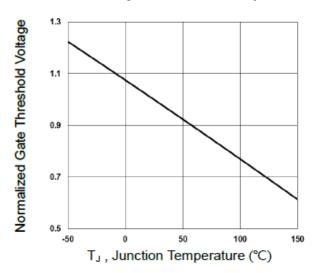
Maximum Safe Operating Area



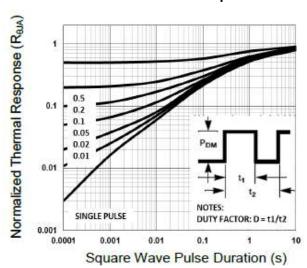
Gate Charge



Threshold Voltage vs. Junction Temperature



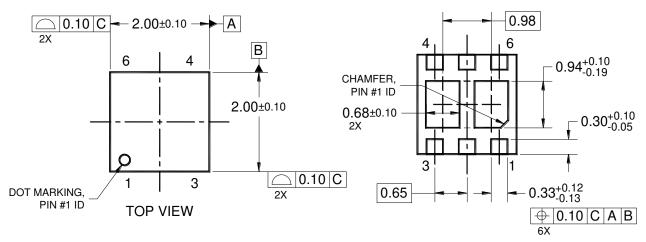
Normalized Thermal Transient Impedance Curve

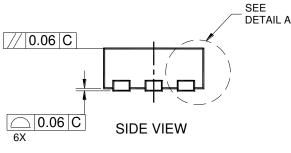


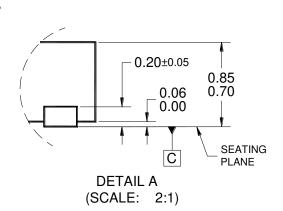


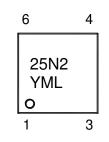
PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

TDFN2x2









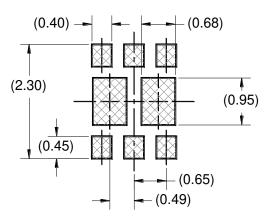
MARKING DIAGRAM (TOP VIEW)

P/N = DEVICE CODE

Y = YEAR CODE

M = MONTH CODE FOR HALOGEN FREE PRODUCT

L = LOT CODE (1~9, A~Z)



SUGGESTED PAD LAYOUT

NOTES: UNLESS OTHERWISE SPECIFIED

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- 2. ALL DIMENSIONS ARE IN MILLIMETERS.
- SEATING PLANE IS DEFINED BY TERMINAL BOTTOM SURFACE ONLY.
- 4. DWG NO. REF: HQ2SD07-TDFN2X2D-003 REV A



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